
Physics and Technology of High-k Gate Dielectrics 4

Editors:

S. Kar

Indian Institute of Technology, Kanpur
Kanpur, India

M. Houssa

IMEC
Leuven, Belgium

H. Iwai

Tokyo Institute of Technology
Tokyo, Japan

S. De Gendt

IMEC
Leuven, Belgium

D. Landheer

National Research Council
Ottawa, Ontario, Canada

D. Misra

New Jersey Institute of Technology
Newark, New Jersey, USA

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